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NGTB60N65FL2WG

IGBT - Field Stop II

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss.

Features

- Extremely Efficient Trench with Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Soft Fast Reverse Recovery Diode
- Optimized for High Speed Switching
- 5 μs Short-Circuit Capability
- These are Pb-Free Devices

Typical Applications

- Solar Inverters
- Uninterruptible Power Supplies (UPS)
- Welding

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-emitter voltage	V_{CES}	650	V
Collector current @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$	I_C	100 60	A
Diode Forward Current @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$	I_F	100 60	A
Diode Pulsed Current T_{PULSE} Limited by T_J Max	I_{FM}	240	A
Pulsed collector current, T_{pulse} limited by T_{Jmax}	I_{CM}	240	A
Short-circuit withstand time $V_{GE} = 15 V$, $V_{CE} = 400 V$, $T_J \leq +150^{\circ}C$	t_{SC}	5	μs
Gate-emitter voltage	V_{GE}	± 20	V
Transient gate-emitter voltage ($T_{PULSE} = 5 \mu s$, $D < 0.10$)		± 30	
Power Dissipation @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$	P_D	595 265	W
Operating junction temperature range	T_J	-55 to +175	$^{\circ}C$
Storage temperature range	T_{stg}	-55 to +175	$^{\circ}C$
Lead temperature for soldering, 1/8" from case for 5 seconds	T_{SLD}	260	$^{\circ}C$

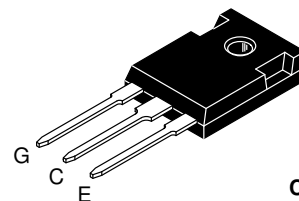
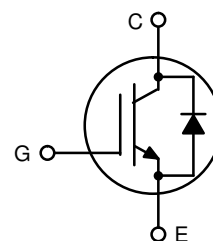
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



ON Semiconductor®

www.onsemi.com

60 A, 650 V
 $V_{CEsat} = 1.64 V$



TO-247
CASE 340L
STYLE 4

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGTB60N65FL2WG	TO-247 (Pb-Free)	30 Units / Rail

NGTB60N65FL2WG

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case, for IGBT	$R_{\theta JC}$	0.28	°C/W
Thermal resistance junction-to-case, for Diode	$R_{\theta JC}$	0.62	°C/W
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	°C/W

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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STATIC CHARACTERISTIC

Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$	$V_{(BR)CES}$	650	–	–	V
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 60\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 60\text{ A}, T_J = 175^\circ\text{C}$	V_{CEsat}	1.50 –	1.64 2.00	2.00 –	V
Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 350\ \mu\text{A}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}$ $V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}, T_J = 175^\circ\text{C}$	I_{CES}	–	– 5.0	0.1 –	mA
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	–	–	200	nA

DYNAMIC CHARACTERISTIC

Input capacitance	$V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{ies}	–	7193	–	pF
Output capacitance		C_{oes}	–	311	–	
Reverse transfer capacitance		C_{res}	–	202	–	
Gate charge total	$V_{CE} = 480\text{ V}, I_C = 60\text{ A}, V_{GE} = 15\text{ V}$	Q_g	–	318	–	nC
Gate to emitter charge		Q_{ge}	–	65	–	
Gate to collector charge		Q_{gc}	–	163	–	

SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Turn-on delay time	$T_J = 25^\circ\text{C}$ $V_{CC} = 400\text{ V}, I_C = 60\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(on)}$	–	117	–	ns	
Rise time		t_r	–	53	–		
Turn-off delay time		$t_{d(off)}$	–	265	–		
Fall time			t_f	–	75	–	mJ
Turn-on switching loss		E_{on}	–	1.59	–		
Turn-off switching loss		E_{off}	–	0.66	–		
Total switching loss		E_{ts}	–	2.25	–		
Turn-on delay time	$T_J = 150^\circ\text{C}$ $V_{CC} = 400\text{ V}, I_C = 60\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(on)}$	–	113	–	ns	
Rise time		t_r	–	55	–		
Turn-off delay time		$t_{d(off)}$	–	277	–		
Fall time			t_f	–	1.0	–	mJ
Turn-on switching loss		E_{on}	–	2.0	–		
Turn-off switching loss		E_{off}	–	1.1	–		
Total switching loss		E_{ts}	–	3.1	–		

DIODE CHARACTERISTIC

Forward voltage	$V_{GE} = 0\text{ V}, I_F = 60\text{ A}$ $V_{GE} = 0\text{ V}, I_F = 60\text{ A}, T_J = 175^\circ\text{C}$	V_F	1.50 –	2.13 2.26	2.80 –	V
Reverse recovery time	$T_J = 25^\circ\text{C}$ $I_F = 60\text{ A}, V_R = 400\text{ V}$ $di_F/dt = 200\text{ A}/\mu\text{s}$	t_{rr}	–	96	–	ns
Reverse recovery charge		Q_{rr}	–	0.39	–	μC
Reverse recovery current		I_{rrm}	–	6.8	–	A
Reverse recovery time	$T_J = 175^\circ\text{C}$ $I_F = 60\text{ A}, V_R = 400\text{ V}$ $di_F/dt = 200\text{ A}/\mu\text{s}$	t_{rr}	–	177	–	ns
Reverse recovery charge		Q_{rr}	–	1.53	–	μC
Reverse recovery current		I_{rrm}	–	13	–	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NGTB60N65FL2WG

TYPICAL CHARACTERISTICS

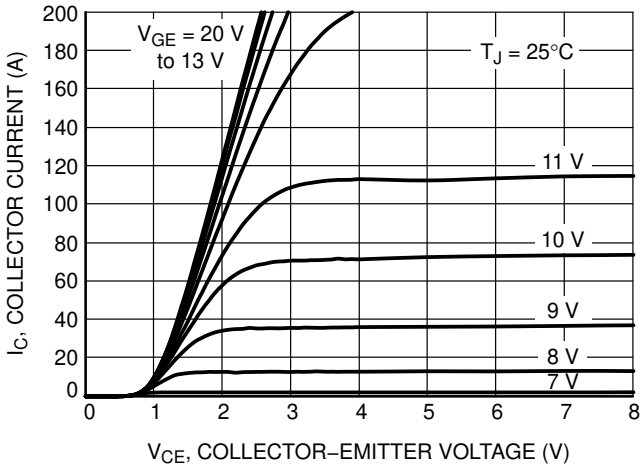


Figure 1. Output Characteristics

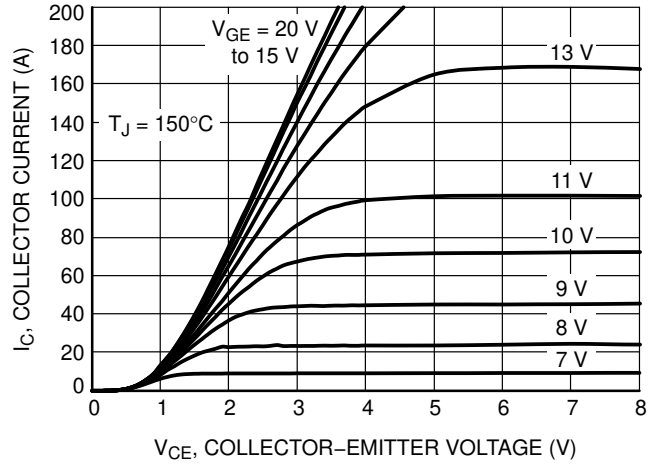


Figure 2. Output Characteristics

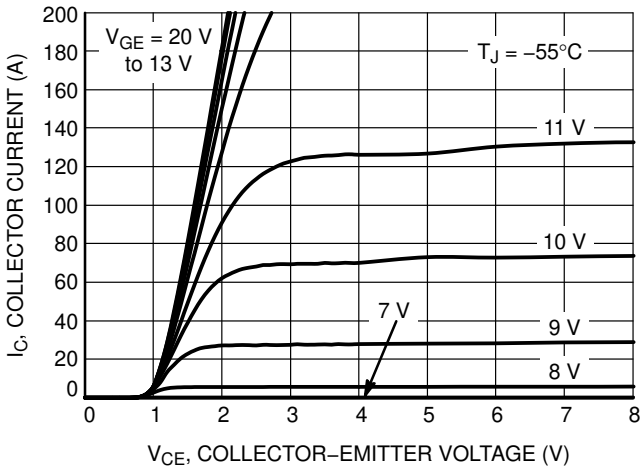


Figure 3. Output Characteristics

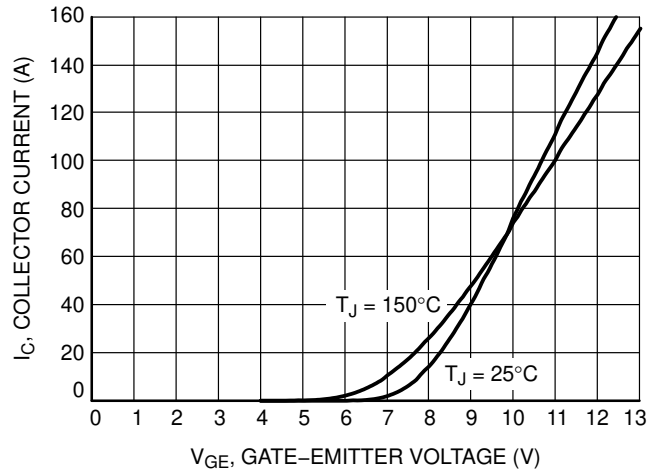


Figure 4. Typical Transfer Characteristics

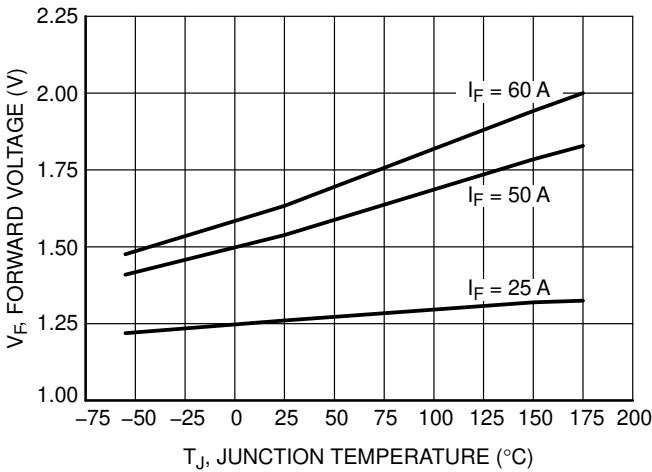


Figure 5. V_F vs. T_J

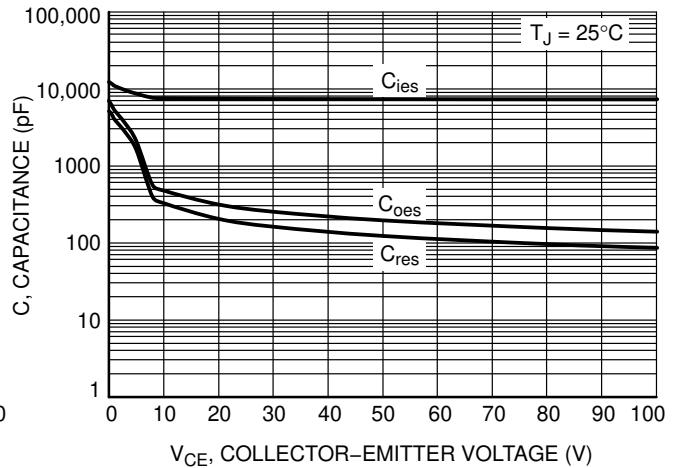


Figure 6. Typical Capacitance

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TYPICAL CHARACTERISTICS

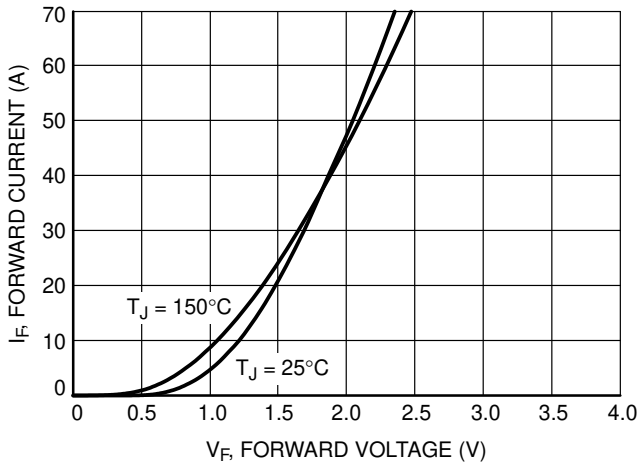


Figure 7. Diode Forward Characteristics

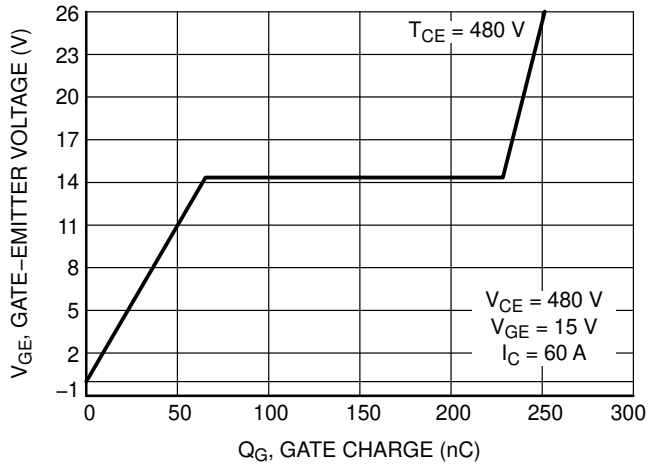


Figure 8. Typical Gate Charge

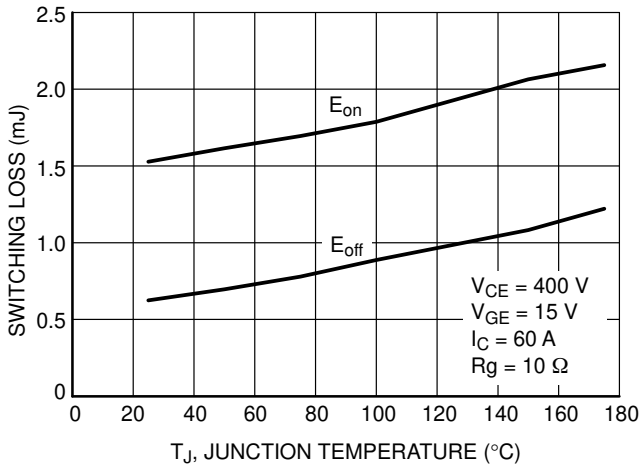


Figure 9. Switching Loss vs. Temperature

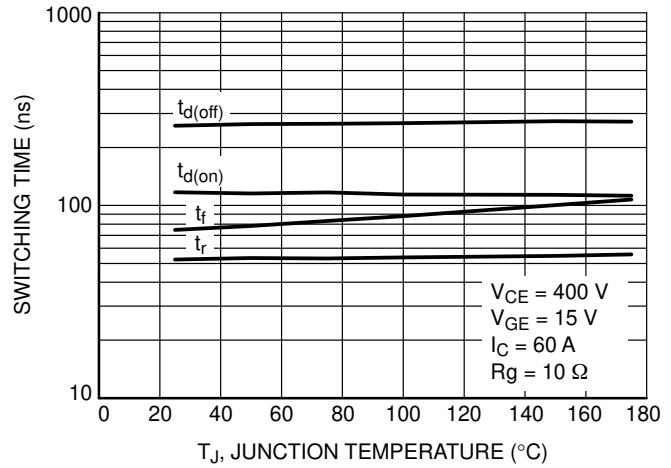


Figure 10. Switching Time vs. Temperature

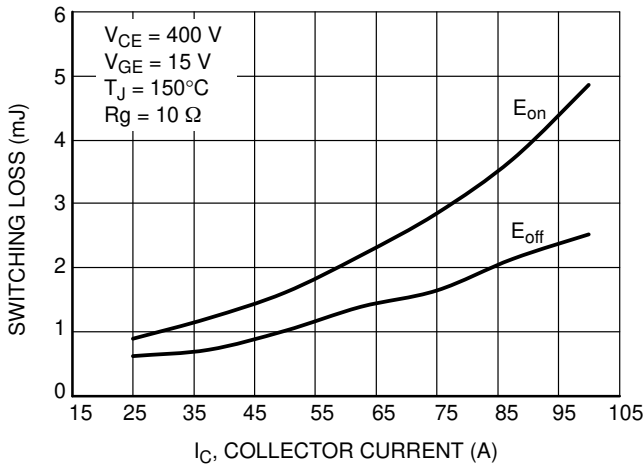


Figure 11. Switching Loss vs. I_C

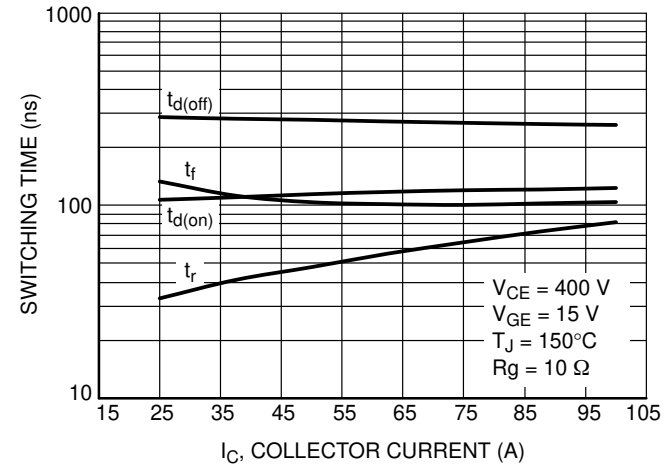


Figure 12. Switching Time vs. I_C

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TYPICAL CHARACTERISTICS

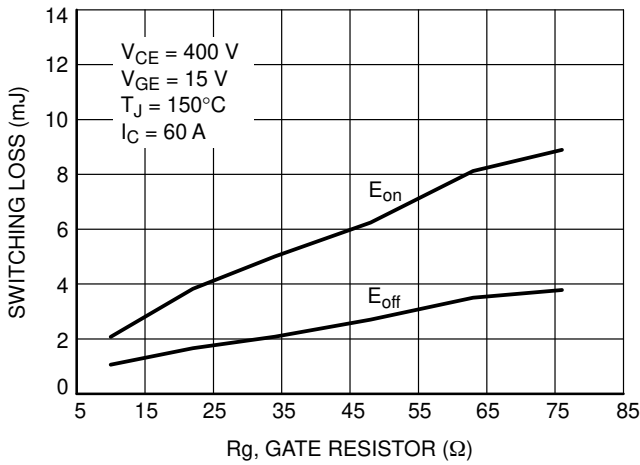


Figure 13. Switching Loss vs. Rg

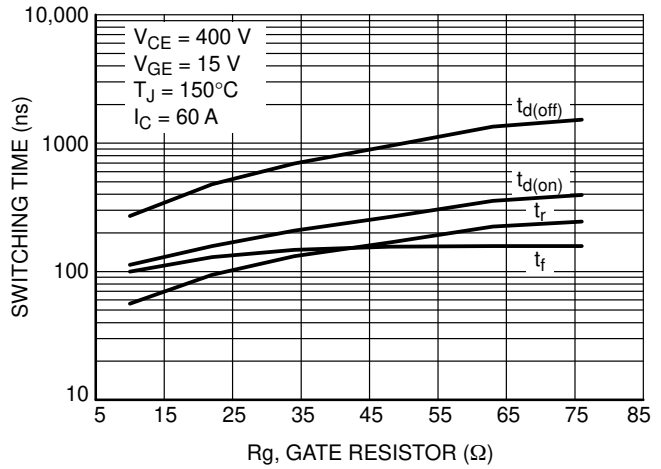


Figure 14. Switching Time vs. Rg

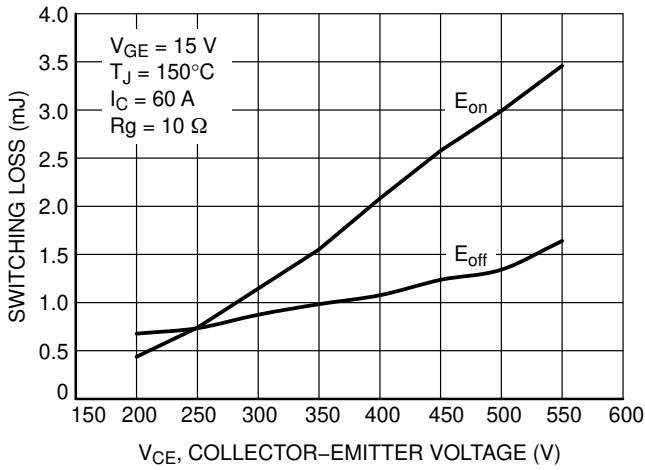


Figure 15. Switching Loss vs. V_{CE}

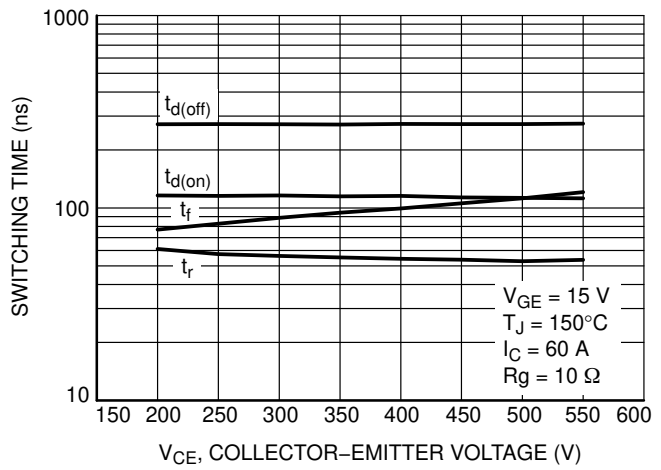


Figure 16. Switching Time vs. V_{CE}

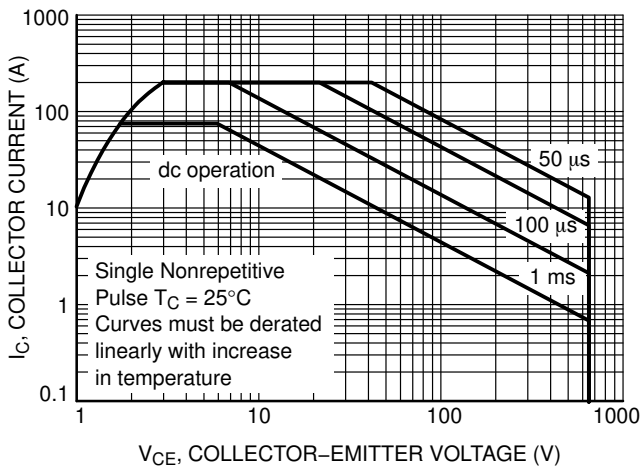


Figure 17. Safe Operating Area

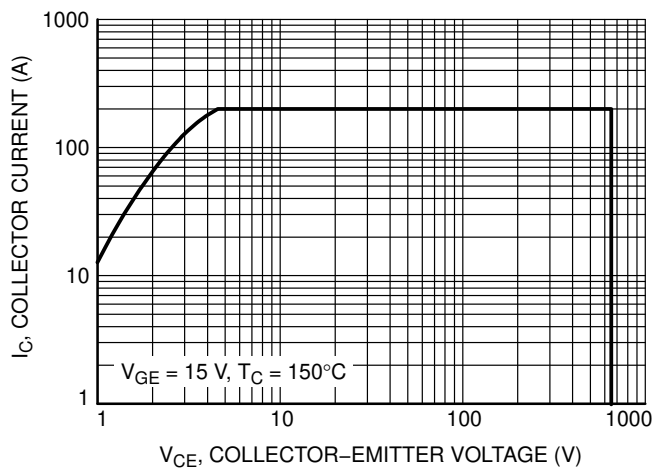


Figure 18. Reverse Bias Safe Operating Area

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TYPICAL CHARACTERISTICS

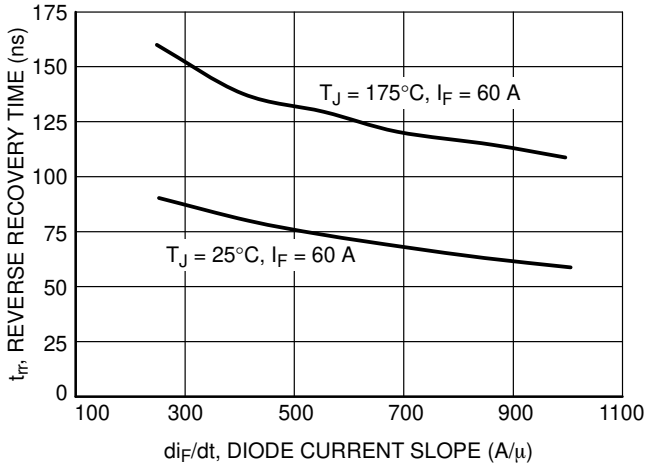


Figure 19. t_{rr} vs. di_F/dt ($V_R = 400\text{ V}$)

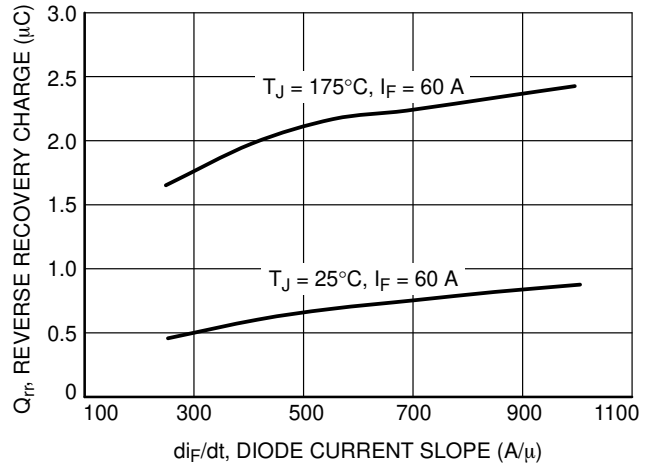


Figure 20. Q_{rr} vs. di_F/dt ($V_R = 400\text{ V}$)

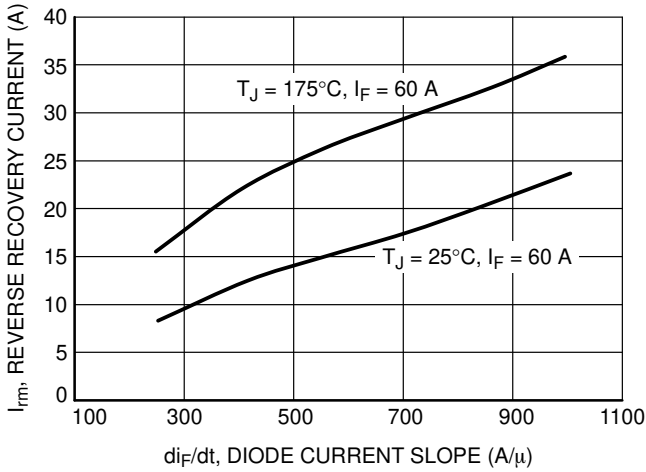


Figure 21. I_{rrm} vs. di_F/dt ($V_R = 400\text{ V}$)

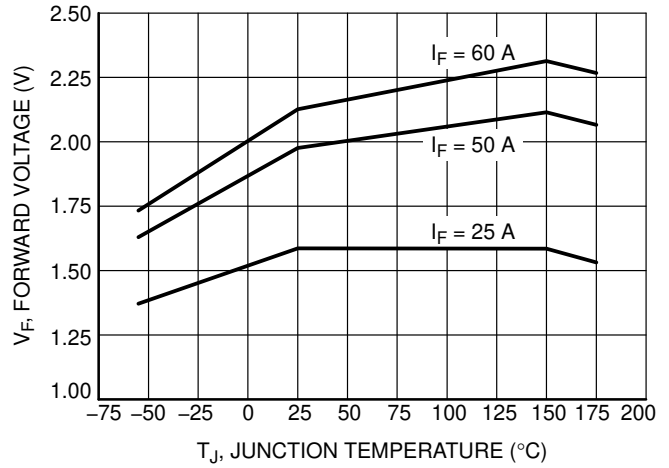


Figure 22. V_F vs. T_J

NGTB60N65FL2WG

TYPICAL CHARACTERISTICS

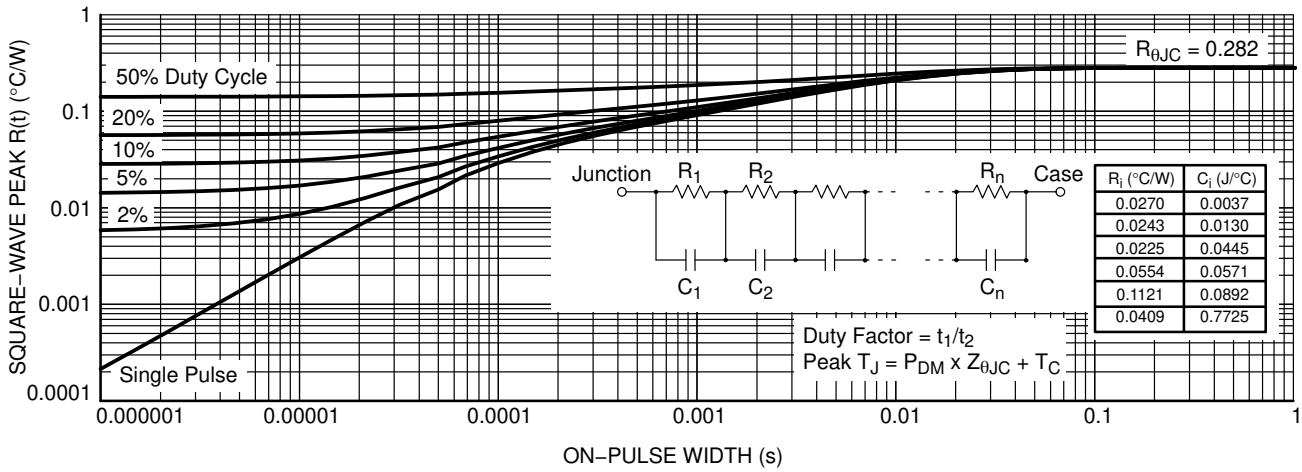


Figure 23. IGBT Transient Thermal Impedance

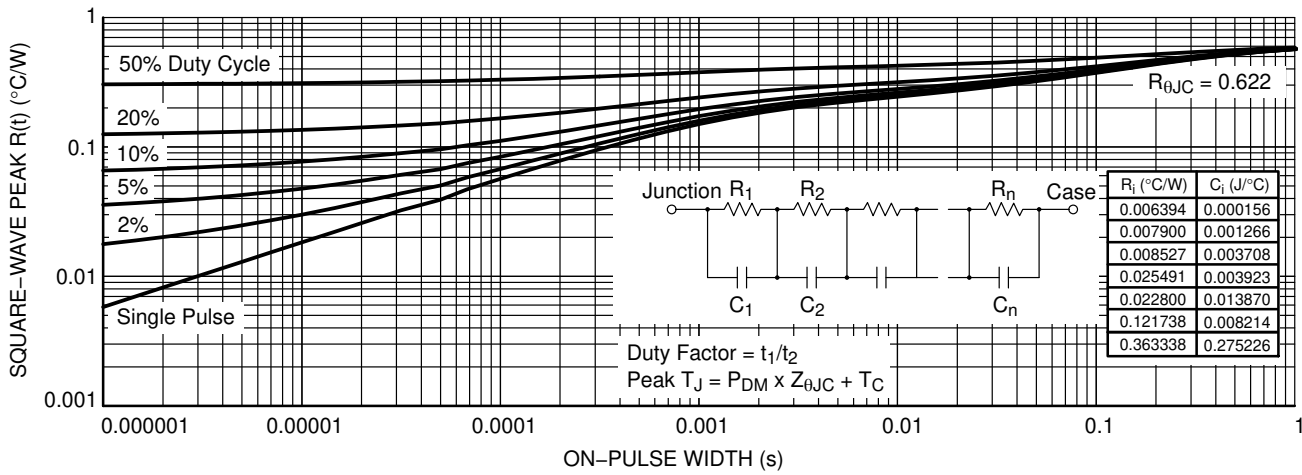
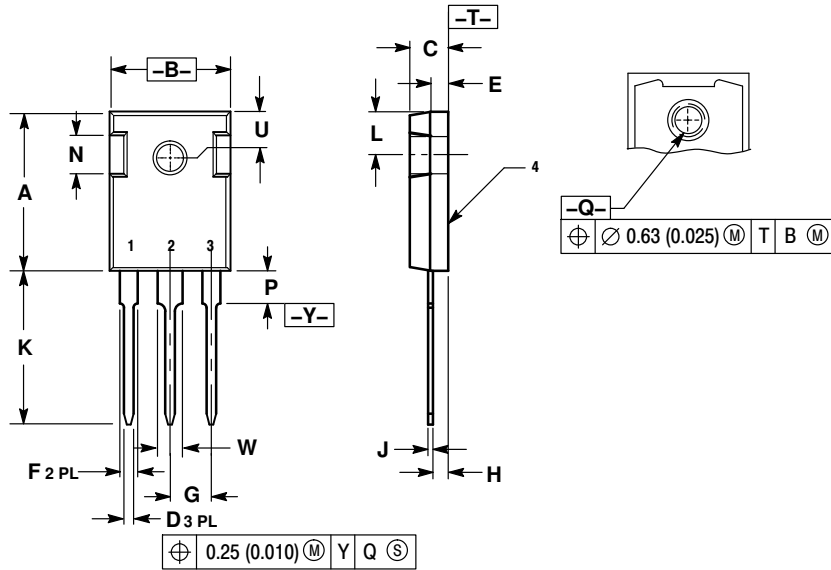


Figure 24. Diode Transient Thermal Impedance

NGTB60N65FL2WG

PACKAGE DIMENSIONS

TO-247
CASE 340L-02
ISSUE F



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	20.32	21.08	0.800	0.830
B	15.75	16.26	0.620	0.640
C	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
E	1.90	2.60	0.075	0.102
F	1.65	2.13	0.065	0.084
G	5.45 BSC		0.215 BSC	
H	1.50	2.49	0.059	0.098
J	0.40	0.80	0.016	0.031
K	19.81	20.83	0.780	0.820
L	5.40	6.20	0.212	0.244
N	4.32	5.49	0.170	0.216
P	---	4.50	---	0.177
Q	3.55	3.65	0.140	0.144
U	6.15 BSC		0.242 BSC	
W	2.87	3.12	0.113	0.123

- STYLE 4:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

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